



DMG3401LSN

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D $T_A = 25^\circ C$
-30V	50mΩ @ $V_{GS} = -10V$	-3.7A
	60mΩ @ $V_{GS} = -4.5V$	-3.3A
	85mΩ @ $V_{GS} = -2.5V$	-2.7A

Description

This new generation Small-Signal enhancement mode MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

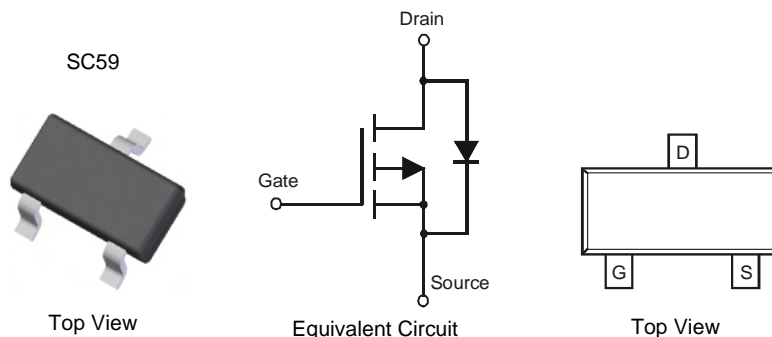
- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

Features

- Low Input Capacitance
- Low On-Resistance
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SC59
- Case Material: Molded Plastic "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

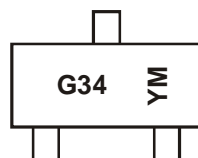


Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3401LSN-7	SC59	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Marking Information



G34 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-3.0	A
		T _A = +70°C		-2.3	
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-3.7	A
		T _A = +70°C		-2.9	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	-30	A
Maximum Body Diode Continuous Current (Note 6)			I _S	-1.5	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P _D	0.8	W
	(Note 6)		1.2	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	159	°C/W
	(Note 6)		105	
Thermal Resistance, Junction to Case	(Note 6)	R _{θJC}	36	°C
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	-1.0	-1.3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	41	50	mΩ	V _{GS} = -10V, I _D = -4A
		-	47	60		V _{GS} = -4.5V, I _D = -3.5A
		-	60	85		V _{GS} = -2.5V, I _D = -2.5A
Forward Transfer Admittance	Y _{fs}	-	12	-	S	V _{DS} = -5V, I _D = -4A
Diode Forward Voltage	V _{SD}	-	-0.8	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	1326	-	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	103	-		
Reverse Transfer Capacitance	C _{rss}	-	71	-		
Gate Resistance	R _g	-	7.3	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	-	11.6	-	nC	V _{DD} = -15V, I _D = -4A
Total Gate Charge (V _{GS} = -10V)	Q _g	-	25.1	-		
Gate-Source Charge	Q _{gs}	-	2	-		
Gate-Drain Charge	Q _{gd}	-	1.7	-		
Turn-On Delay Time	t _{D(on)}	-	8	-	nS	V _{DS} = -15V, V _{GS} = -10V, R _{GEN} = 6Ω, R _L = 3.75Ω
Turn-On Rise Time	t _r	-	13	-		
Turn-Off Delay Time	t _{D(off)}	-	71	-		
Turn-Off Fall Time	t _f	-	38	-		

- Notes:
3. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 4. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 5. Short duration pulse test used to minimize self-heating effect.
 6. Guaranteed by design. Not subject to production testing